

IN THE CLAIMS:

Please amend the claims as follows:

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8. (Amended) An ohmic contact in a semiconductor device which is formed on a semiconductor material, the ohmic contact comprising a mixture of p-type semiconductor oxide and metal.

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9. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a single oxide.

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10. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a mixture of various oxides.

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11. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a solid solution of various oxides.

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12. (Amended) The ohmic contact as claimed in claim 8 wherein the semiconductor material is p-type $\text{Al}_x\text{Ga}_y\text{In}_z\text{N}$, and $0 < x, y, z < 1$, and $x + y + z = 1$.

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13. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide is one of NiO , MnO , FeO , Fe_2O_3 , CoO , CrO , Cr_2O_3 , CrO_2 , CuO , Cu_2O , SnO , Ag_2O , CuAlO_2 , SrCu_2O_2 and PdO .

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14. (Amended) The ohmic contact as claimed in claim 8 wherein the metal is Au, Pt, Rh, Ru, or Ir.

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15. (Amended) The ohmic contact as claimed in claim 12 wherein the semiconductor material is p-type GaN .

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16. (Amended) An ohmic contact in a semiconductor device, which is formed on a semiconductor material, the ohmic contact comprising a layer of p-type semiconductor oxide and a conductive layer.

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17. (Amended) The ohmic contact as claimed in claim 16 wherein the semiconductor material is p-type $\text{Al}_x\text{Ga}_y\text{In}_z\text{N}$, and $0 < x, y, z < 1$, and $x + y + z = 1$.

1 18. (Amended) The ohmic contact as claimed in claim 16 wherein the p-type
2 semiconductor oxide is one of NiO, MnO, FeO, Fe₂O₃, CoO, CrO, Cr₂O₃, CrO₂, CuO, Cu₂O,
3 SnO, Ag₂O, CuAlO₂, SrCu₂O₂, LaMnO₃, YBa₂Cu₄O₈ and PdO.

1 19. (Amended) The ohmic contact as claimed in claim 16 wherein the layer of
2 semiconductor oxide includes a single oxide layer.

1 20. (Amended) The ohmic contact as claimed in claim 16 wherein the layer of
2 semiconductor oxide includes a plurality of layers of oxides of the same conductivity type.

1 21. (Amended) The ohmic contact as claimed in claim 16 wherein the layer of
2 semiconductor oxide includes a mixture layer of various oxides.

1 22. (Amended) The ohmic contact as claimed in claim 16 wherein the layer of
2 semiconductor oxide includes a solid solution layer consisting of various oxides.

1 23. (Amended) The ohmic contact as claimed in claim 16 wherein the
2 conductive layer includes a single metal layer.

1 24. (Amended) The ohmic contact as claimed in claim 16 wherein the
2 conductive layer includes a plurality of metal layers.

1 25. (Amended) The ohmic contact as claimed in claim 16 wherein the
2 conductive layer is a transparent conductive film.

1 26. (Amended) The ohmic contact as claimed in claim 17 wherein the
2 semiconductor material is p-type GaN.

1 27. (Amended) The ohmic contact as claimed in claim 25 wherein the
2 transparent conductive film is conductive oxide, including indium-tin oxide, ZnO and ZnO doped
3 with Ga, In, Al or Ce.

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